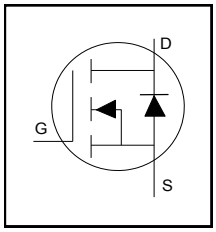
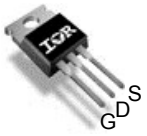
HEXFET® Power MOSFET

Application
- Optimized for UPS/Inverter Applications
- Low Voltage Power Tools

Benefits
- Best in Class Performance for UPS/Inverter Applications
- Very Low RDS(on) at 4.5V VGS
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current
- Lead-Free, RoHS Compliant



V_{DSS}	30	V
$R_{DS(on)}$ max (@ V_{GS} = 10V)	2.4	mΩ
(@ V_{GS} = 4.5V)	3.2	
Q_g (typical)	40	nC
I_D (Silicon Limited)	171⑥	A
I_D (Package Limited)	130A	



TO-220Pak

G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRLB8314PbF	TO-220Pak	Tube	50	IRLB8314PbF

Absolute Maximium Rating

Symbol	Parameter	Max.	Units
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	171⑥	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	120	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Package Limited)	130	
I_{DM}	Pulsed Drain Current ①	664	
P_D @T_C = 25°C	Maximum Power Dissipation	125	W
P_D @T_C = 100°C	Maximum Power Dissipation	63	W
	Linear Derating Factor	0.83	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	–––	1.2	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat Greased Surface	0.50	–––	
$R_{\theta JA}$	Junction-to-Ambient	–––	62	

Notes ① through ④ are on page 8

Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	14	—	mV/°C	Reference to 25°C, I_D = 1mA ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	1.9	2.4	mΩ	V_{GS} = 10V, I_D = 68A ③
		—	2.6	3.2		V_{GS} = 4.5V, I_D = 68A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.2	1.7	2.2	V	V_{DS} = V_{GS}, I_D = 100µA
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-7.0	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	µA	V_{DS} =24 V, V_{GS} = 0V
		—	—	150		V_{DS} =24V,V_{GS} = 0V,T_J =125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
gfs	Forward Transconductance	307	—	—	S	V_{DS} = 15V, I_D =68A
Q_g	Total Gate Charge	—	40	60	nC	V_{DS} = 15V V_{GS} = 4.5V I_D = 68A
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	6.8	—		
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	13	—		
Q_{gd}	Gate-to-Drain Charge	—	8.7	—		
Q_{godr}	Gate Charge Overdrive	—	11.5	—		
Q_{sw}	Switch Charge (Qgs2 + Qgd)		21.7			
R_G	Gate Resistance	—	1.7	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	19	—	ns	V_{DD} = 15V I_D = 68A R_G= 1.8Ω V_{GS} = 4.5V③
t_r	Rise Time	—	142	—		
$t_{d(off)}$	Turn-Off Delay Time	—	32	—		
t_f	Fall Time	—	72	—		
C_{iss}	Input Capacitance	—	5050	—	pF	V_{GS} = 0V V_{DS} = 15V f = 1.0MHz
C_{oss}	Output Capacitance	—	890	—		
C_{rss}	Reverse Transfer Capacitance	—	500	—		

Avalanche Characteristics

$E_{AS\ (Thermally\ limited)}$	Single Pulse Avalanche Energy ②	180	mJ
$E_{AS\ (tested)}$	Single Pulse Avalanche Energy Tested Value ⑤	900	
I_{AR}	Avalanche Current ①	68	A
E_{AR}	Repetitive Avalanche Energy ①	12.5	mJ

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)①	—	—	171⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	664		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	T_J = 25°C,I_S = 68A,V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	—	21	31	ns	T_J = 25°C I_F = 68A ,V_{DD}=15V
Q_{rr}	Reverse Recovery Charge	—	54	81	nC	di/dt = 430A/µs ③

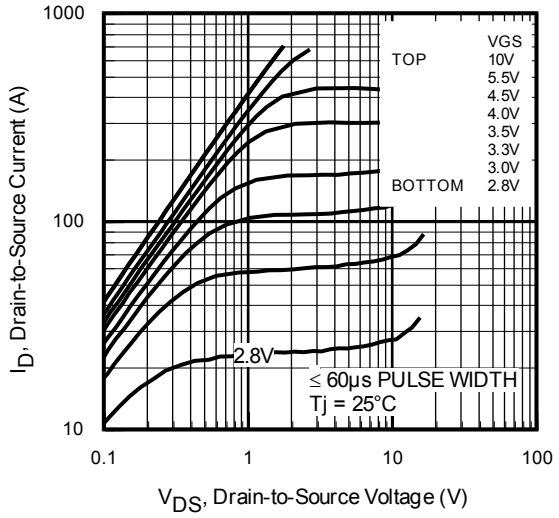


Fig 1. Typical Output Characteristics

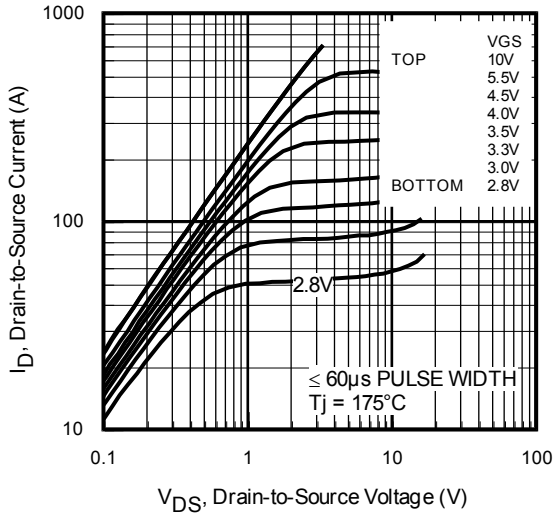


Fig 2. Typical Output Characteristics

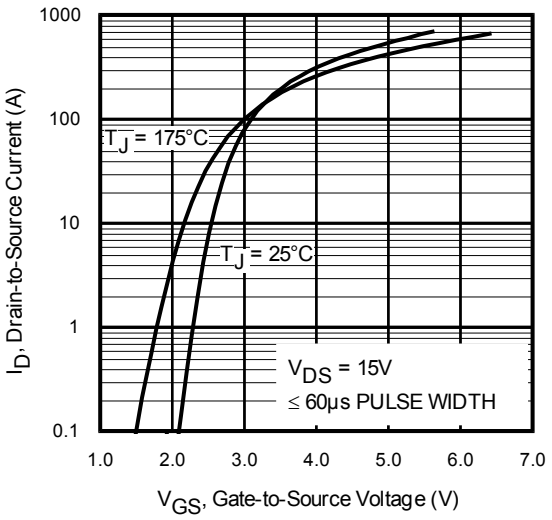


Fig 3. Typical Transfer Characteristics

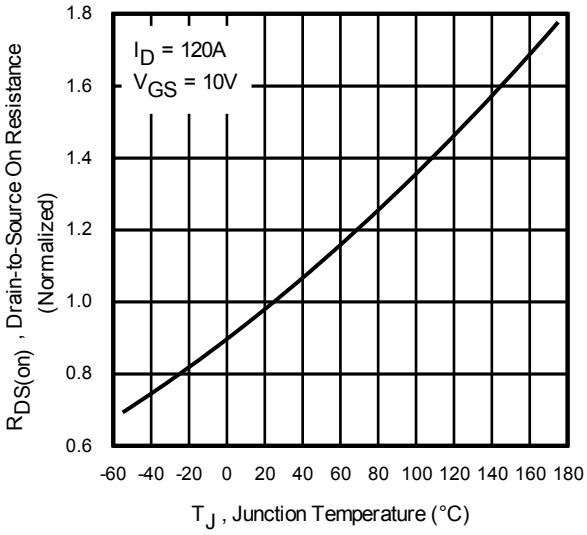


Fig 4. Normalized On-Resistance vs. Temperature

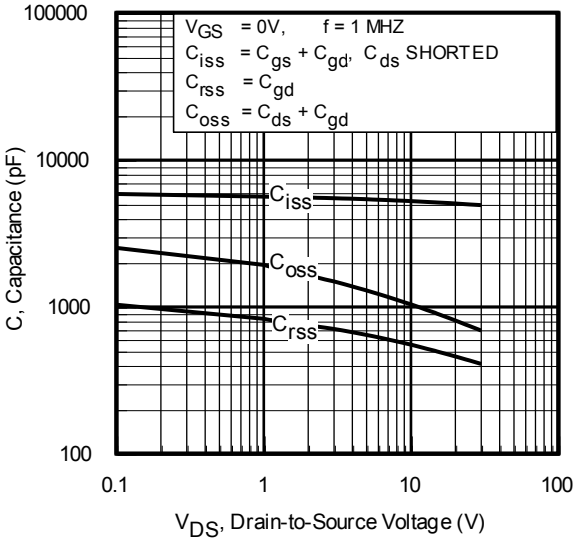


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

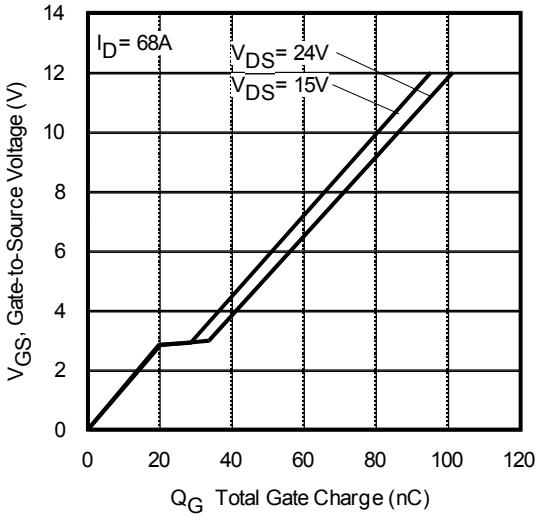


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

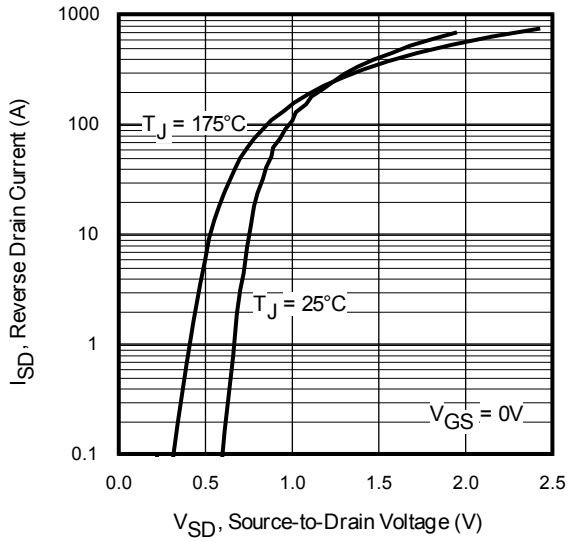


Fig 7. Typical Source-Drain Diode Forward Voltage

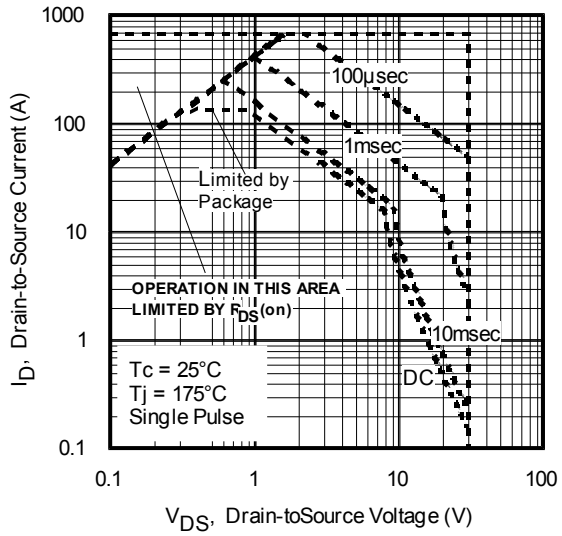


Fig 8. Maximum Safe Operating Area

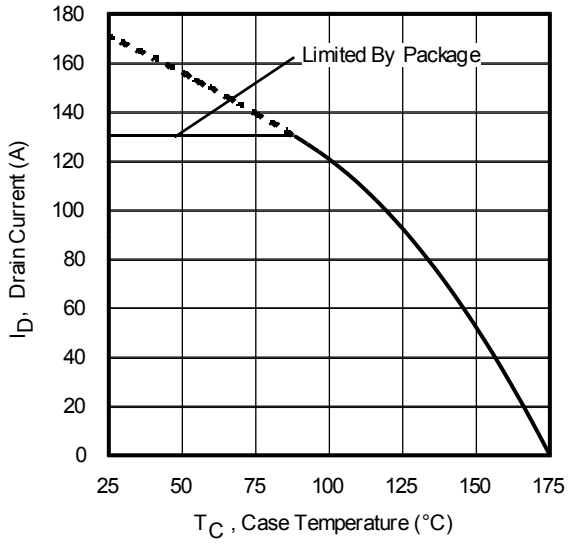


Fig 9. Maximum Drain Current vs. Case Temperature

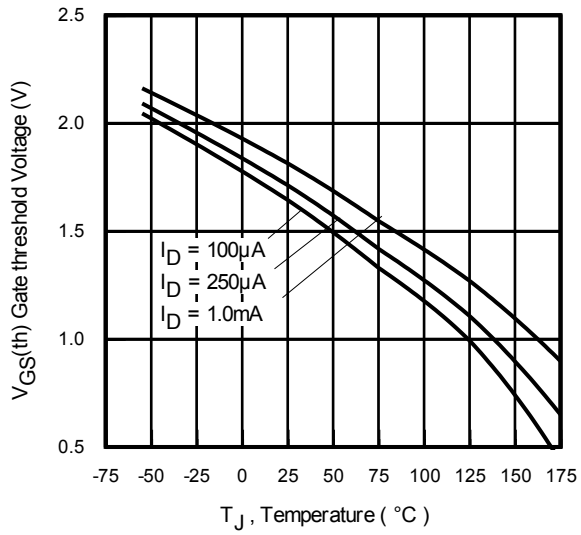


Fig 10. Threshold Voltage vs. Temperature

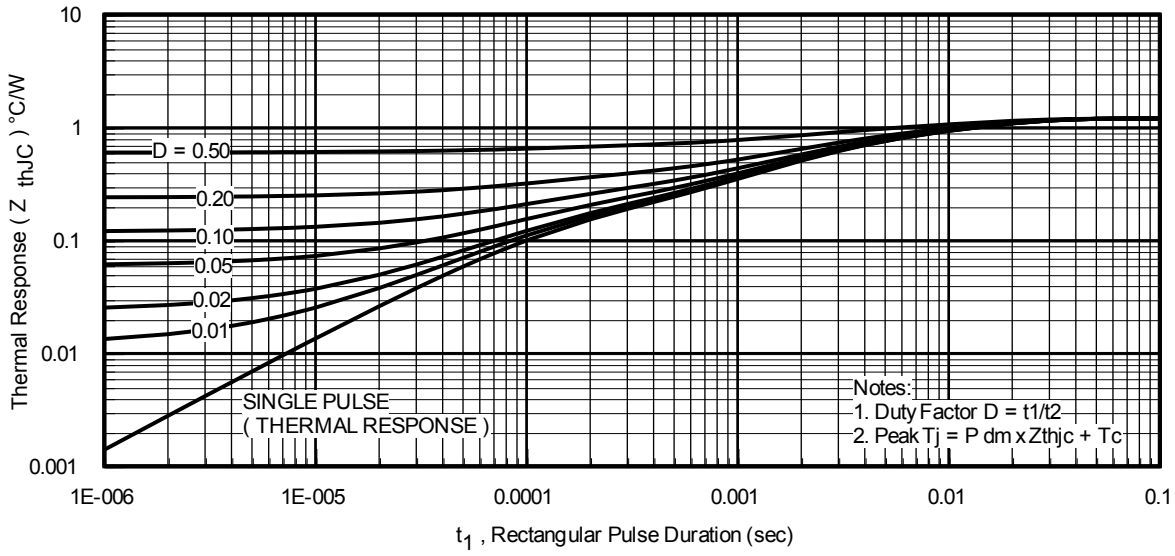


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

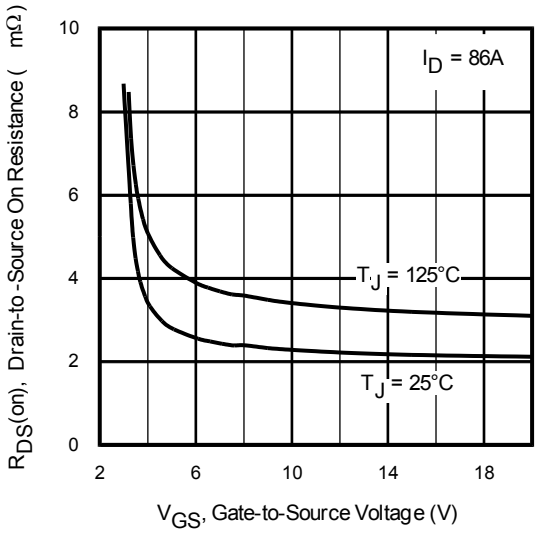


Fig 12. Typical On-Resistance vs. Gate Voltage

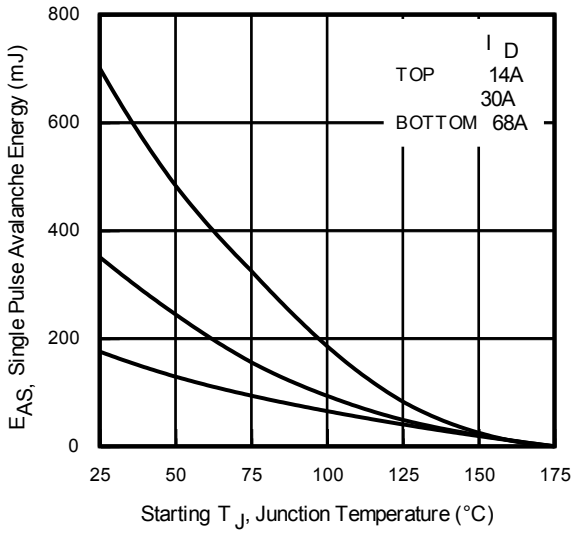


Fig 14. Maximum Avalanche Energy vs. Drain Current

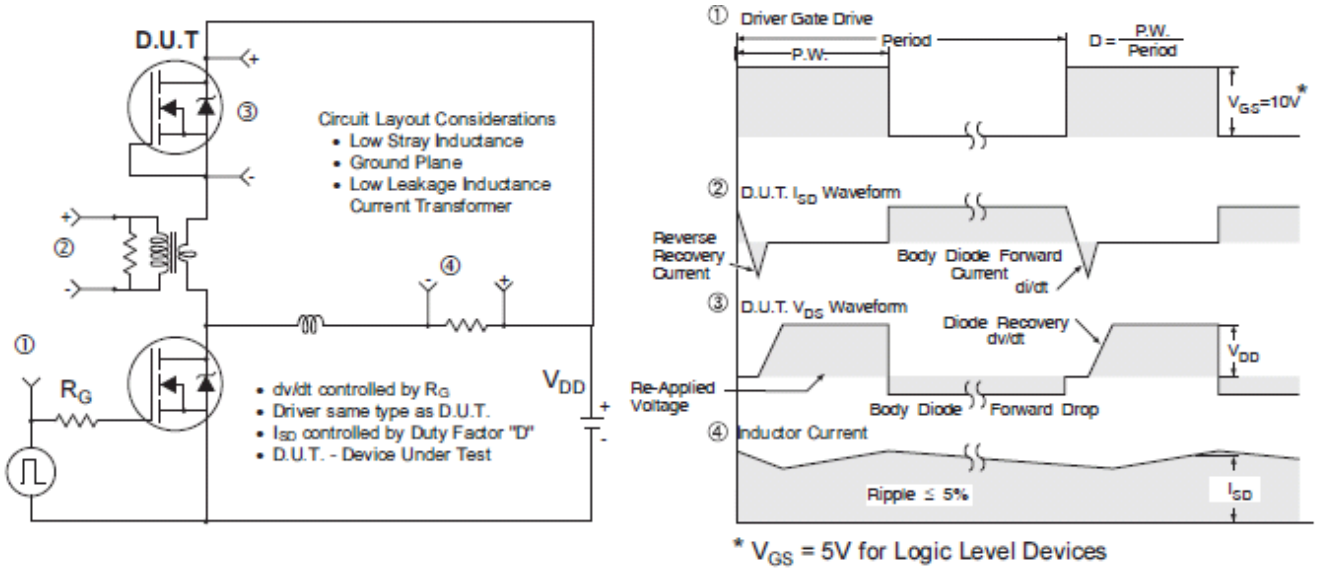


Fig 18. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

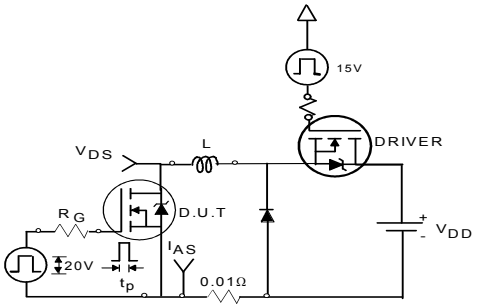


Fig 19a. Unclamped Inductive Test Circuit

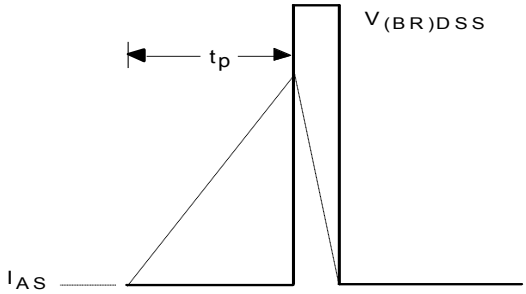


Fig 19b. Unclamped Inductive Waveforms

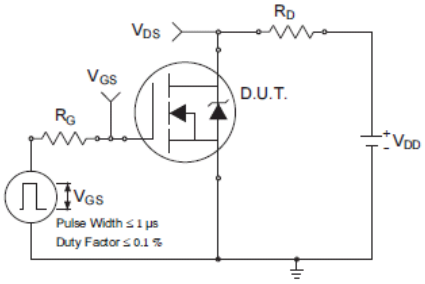


Fig 20a. Switching Time Test Circuit

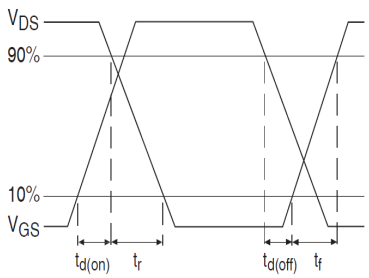


Fig 20b. Switching Time Waveforms

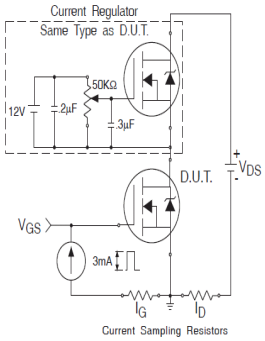


Fig 21a. Gate Charge Test Circuit

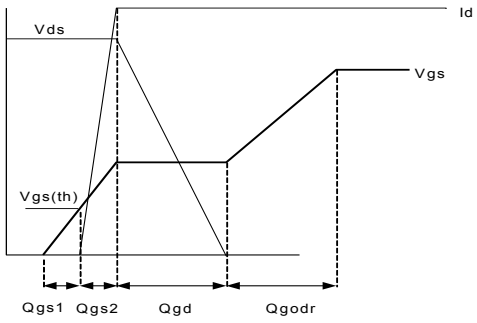
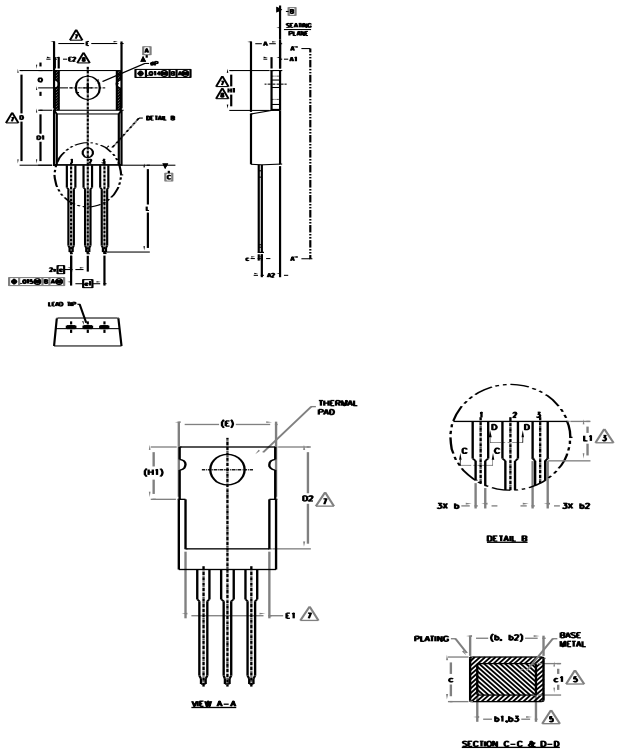


Fig 21b. Gate Charge Waveform

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
6.- CONTROLLING DIMENSION : INCHES.
7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

LEAD ASSIGNMENTS

HEXFET

1.- GATE
2.- DRAIN
3.- SOURCE

IGBTs, CoPACK

1.- GATE
2.- COLLECTOR
3.- EMITTER

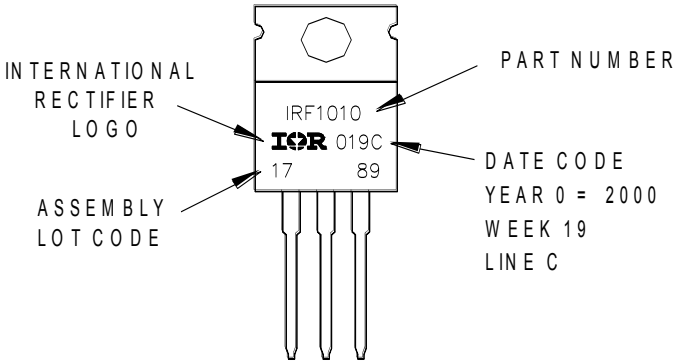
DIODES

1.- ANODE
2.- CATHODE
3.- ANODE

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 2000
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead - Free"



TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information†

Qualification Level	Industrial (per JEDEC JESD47F) ††	
Moisture Sensitivity Level	TO-220	N/A
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability/

†† Applicable version of JEDEC standard at the time of product release.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.067mH, R_G = 50Ω, I_{AS} = 68A, V_{GS} =10V.

③ Pulse width ≤ 400µs; duty cycle ≤ 2%.

④ R_θ is measured at T_J approximately 90°C.

⑤ This value determined from sample failure population, starting T_J =25°C, L=0.5mH, R_G = 50Ω, I_{AS} =60A, V_{GS} =10V.

⑥ Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 130A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140).

International IOR Rectifier

IR WORLD HEADQUARTERS: 101N Sepulveda Blvd, El Segundo, California 90245, USA

To contact International Rectifier, please visit http://www.irf.com/whoto-call/

